

# **Session WE2A**

## **Microwave Power Devices and Amplifiers II**

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2A

**Chairman:**

**B. Bayraktaroglu**  
Westinghouse ESG

This session includes papers regarding power performance, linearity, ruggedness, fabrication, and thermal properties of high power microwave devices and amplifiers. A wide range of device technologies are discussed with emphasis on transitioning from research to applications. The frequency range is from 1 GHz in commercial applications using GaAs HFETs to  $> 35$  GHz in millimeter-wave system applications using InP-based HEMTs.

**10:30 a.m.–12:00 p.m., Wednesday, May 17, 1995**  
**Room A1**